

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

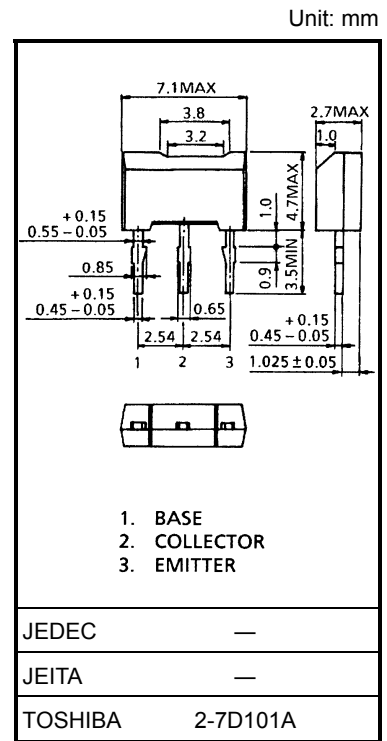
# 2SC3669

Power Amplifier Applications  
Power Switching Applications

- Low collector saturation voltage:  $V_{CE(sat)} = 0.5\text{ V (max)}$  ( $I_C = 1\text{ A}$ )
- High-speed switching:  $t_{stg} = 1.0\text{ }\mu\text{s (typ.)}$
- Complementary to 2SA1429

## Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

| Characteristics             | Symbol    | Rating     | Unit             |
|-----------------------------|-----------|------------|------------------|
| Collector-base voltage      | $V_{CBO}$ | 80         | V                |
| Collector-emitter voltage   | $V_{CEO}$ | 80         | V                |
| Emitter-base voltage        | $V_{EBO}$ | 5          | V                |
| Collector current           | $I_C$     | 2          | A                |
| Base current                | $I_B$     | 1          | A                |
| Collector power dissipation | $P_C$     | 1000       | mW               |
| Junction temperature        | $T_j$     | 150        | $^\circ\text{C}$ |
| Storage temperature range   | $T_{stg}$ | -55 to 150 | $^\circ\text{C}$ |



Weight: 0.2 g (typ.)

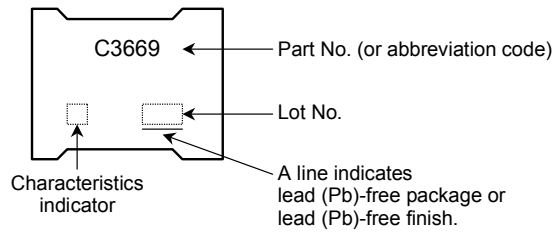
## Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

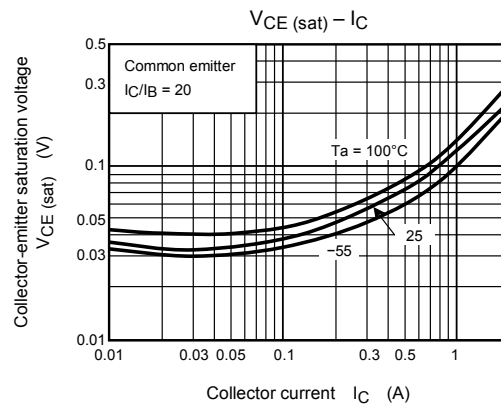
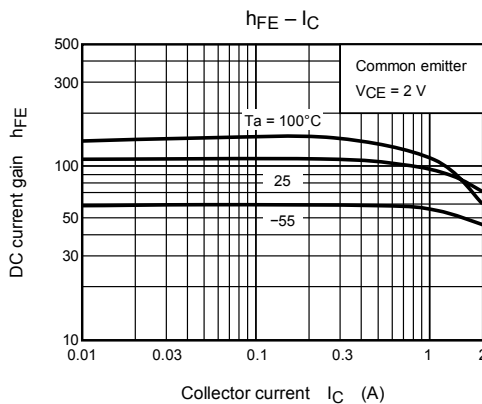
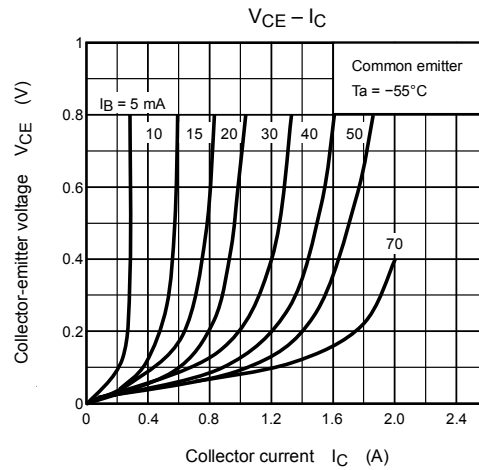
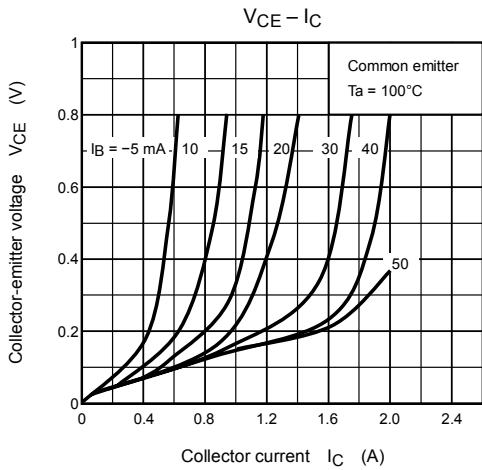
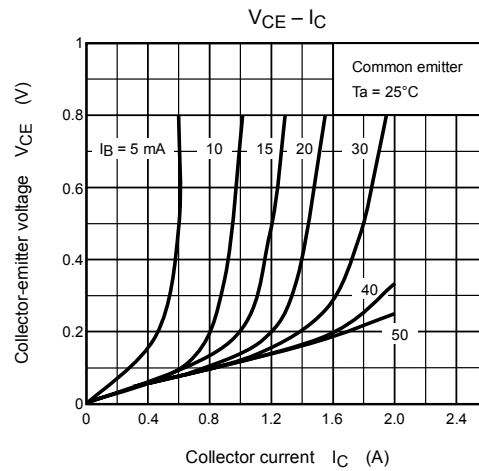
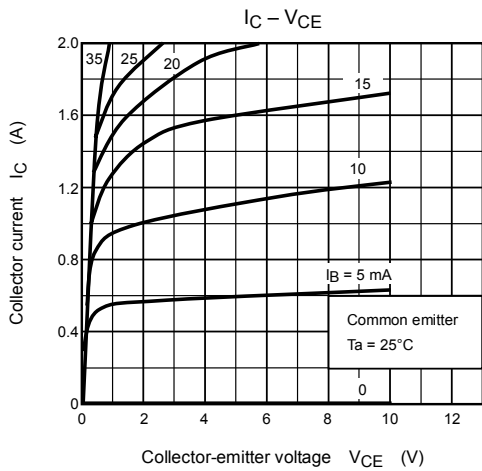
| Characteristics                      | Symbol                | Test Condition                                    | Min | Typ. | Max | Unit          |
|--------------------------------------|-----------------------|---|-----|------|-----|---------------|
| Collector cut-off current            | $I_{CBO}$             | $V_{CB} = 80\text{ V}, I_E = 0$                   | —   | —    | 1.0 | $\mu\text{A}$ |
| Emitter cut-off current              | $I_{EBO}$             | $V_{EB} = 5\text{ V}, I_C = 0$                    | —   | —    | 1.0 | $\mu\text{A}$ |
| Collector-emitter breakdown voltage  | $V_{(BR)CEO}$         | $I_C = 10\text{ mA}, I_B = 0$                     | 80  | —    | —   | V             |
| DC current gain                      | $h_{FE(1)}$<br>(Note) | $V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$         | 70  | —    | 240 |               |
|                                      | $h_{FE(2)}$           | $V_{CE} = 2\text{ V}, I_C = 1.5\text{ A}$         | 40  | —    | —   |               |
| Collector-emitter saturation voltage | $V_{CE(sat)}$         | $I_C = 1\text{ A}, I_B = 0.05\text{ A}$           | —   | 0.15 | 0.5 | V             |
| Base-emitter saturation voltage      | $V_{BE(sat)}$         | $I_C = 1\text{ A}, I_B = 0.05\text{ A}$           | —   | 0.9  | 1.2 | V             |
| Transition frequency                 | $f_T$                 | $V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$         | —   | 100  | —   | MHz           |
| Collector output capacitance         | $C_{ob}$              | $V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$ | —   | 30   | —   | pF            |
| Switching time                       | Turn-on time          | $t_{on}$  | —   | 0.2  | —   | $\mu\text{s}$ |
|                                      | Storage time          | $t_{stg}$   | —   | 1.0  | —   |               |
|                                      | Fall time             | $t_f$   | —   | 0.2  | —   |               |

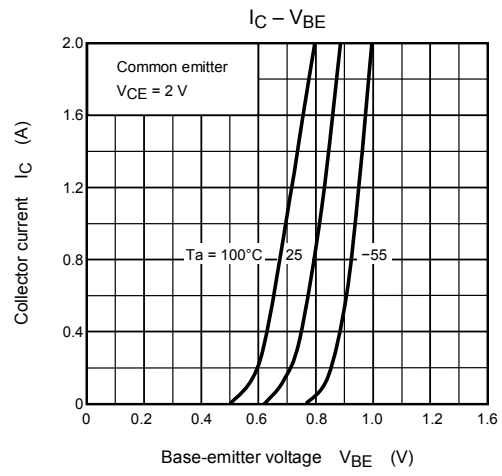
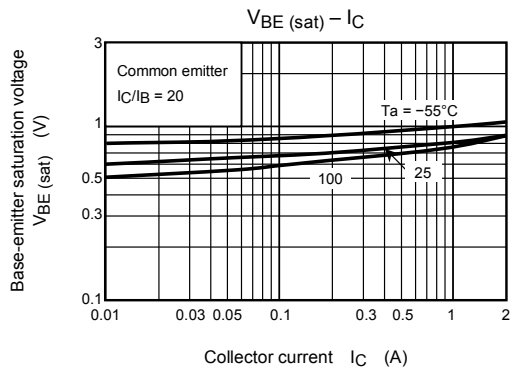
$I_{B1} = -I_{B2} = 0.05\text{ A}, \text{ duty cycle } \leq 1\%$

Note:  $h_{FE(1)}$  classification O: 70 to 140, Y: 120 to 240

## Marking







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